## Method for fabricating a semiconductor structure including a

## Method for fabricating a semiconductor structure including a metal oxide interface with silicon

Abstract	
Equivalents:	CN1302080
EC Classification:	C30B25/02+29/32; C30B25/02+29/16
EC Classification:	C30B25/02
IPC Classification:	C30B25/02; C30B29/16
Priority Number(s):	US19990425945 19991025
Application Number:	EP20000122969 20001023
Requested Patent:	□ <u>JP2001189312</u>
Applicant(s):	MOTOROLA INC (US)
Inventor(s):	RAMDANI JANAL (US); YU ZHIYI JIMMY (US); DROOPAD RAVINDRANATH (US)
Publication date:	2001-05-02
Patent Number:	□ <u>EP1096042</u>
	nteriere with silicon

A method of fabricating a semiconductor structure including the steps of providing a silicon substrate (10) having a surface (12), forming on the surface (12) of the silicon substrate (10), by atomic layer deposition (ALD), a seed layer (20;20') characterised by a silicate material and forming, by atomic layer deposition (ALD) one or more layers of a high dielectric constant oxide (40) on the seed layer (20;20').